

1SV121

Silicon Epitaxial Planar PIN Diode for High Frequency Attenuator

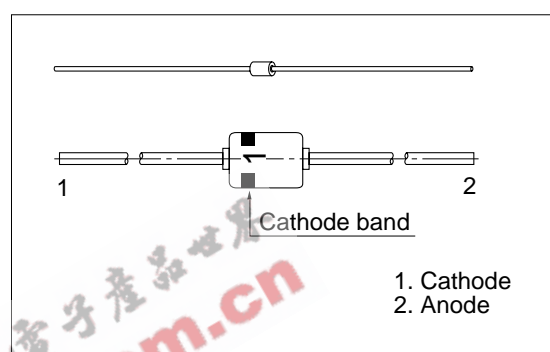
HITACHI

Rev. 0
Oct. 1995**Features**

- Low capacitance.(C=0.7pF max)
- Small glass package (MHD) enables easy mounting and high reliability.

Ordering Information

Type No.	Cathode band	Mark	Package Code
1SV121	Verdure	1	MHD

Outline**Absolute Maximum Ratings (Ta = 25°C)**

Item	Symbol	Value	Unit
Reverse voltage	V_R	100	V
Forward current	I_F	100	mA
Power dissipation	P_d	250	mW
Junction temperature	T_j	175	°C
Storage temperature	T_{stg}	-65 to +175	°C

Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Forward voltage	V_F	—	—	1.1	V	$I_F = 50 \text{ mA}$
Reverse current	I_R	—	—	100	nA	$V_R = 30 \text{ V}$
Capacitance	C	—	—	0.7	pF	$V_R = 50 \text{ V}, f = 1 \text{ MHz}$
Forward resistance	r_{f1}	1.0	—	—	K Ω	$I_F = 10 \text{ }\mu\text{A}, f = 100 \text{ MHz}$
	r_{f2}	—	—	10	Ω	$I_F = 10 \text{ mA}, f = 100 \text{ MHz}$

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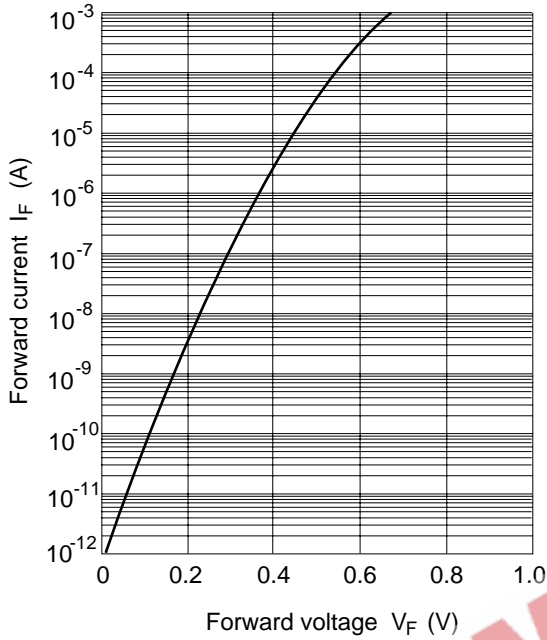


Fig.1 Forward current Vs. Forward voltage

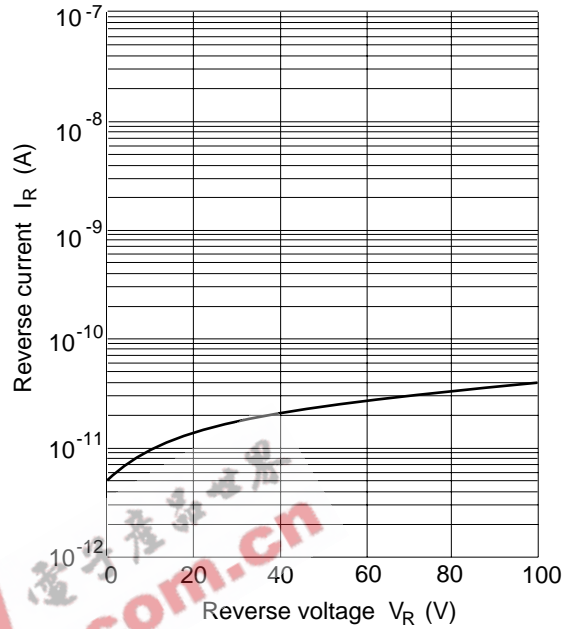


Fig.2 Reverse current Vs. Reverse voltage

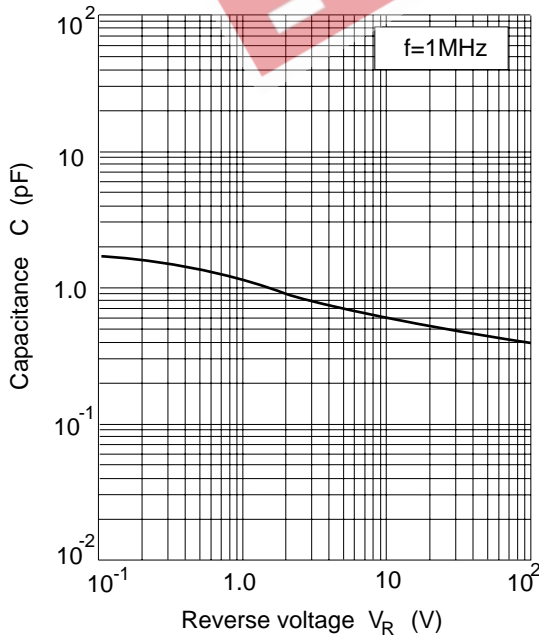


Fig.3 Capacitance Vs. Reverse voltage

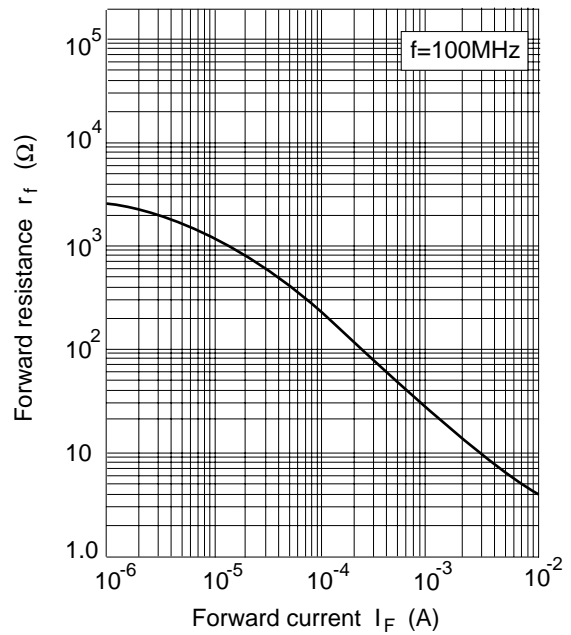


Fig.4 Forward resistance Vs. Forward current

Package Dimensions

Unit: mm

